

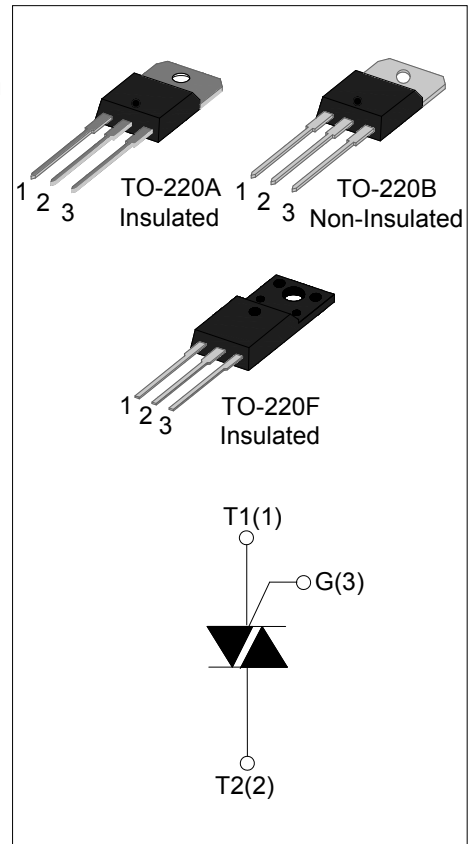
DESCRIPTION:

With high ability to withstand the shock loading of large current, YR BTA/BTB16 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

From all three terminals to external heatsink, YR BTA/BTB16 provides a rated insulation voltage of 2500 Vrms, complying with UL standards .

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage($T_j=25^{\circ}C$)	V_{RRM}	800	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-220A Ins ($T_C=80^{\circ}C$)	16	A
	TO-220F Ins ($T_C=78^{\circ}C$)		

BTA/BTB16 TRIACs

Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	160	A
I^2t value for fusing ($t_p=10ms$)	I^2t	128	A^2s
Rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	100	$A/\mu s$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	mA
V_{GT}		I - II -III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	70	mA
		II		120	
I_H	$I_T=100mA$		MAX	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$		MIN	1000	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=20A t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.9	$^\circ C/W$
		TO-220B(Non-Ins)	1.9	
		TO-220F(Ins)	2.9	

FIG.1: Maximum power dissipation versus RMS on-state current

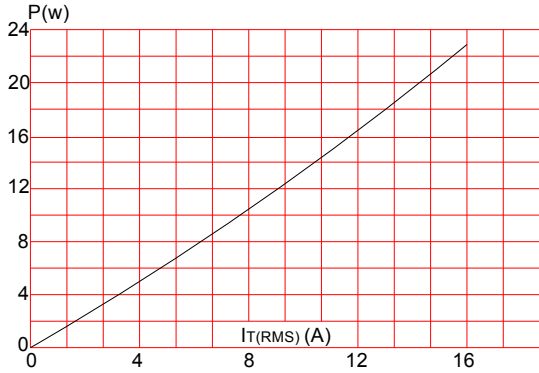


FIG.2: RMS on-state current versus case temperature

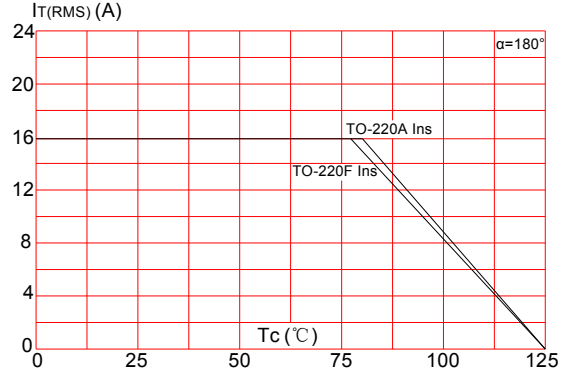


FIG.3: Surge peak on-state current versus number of cycles

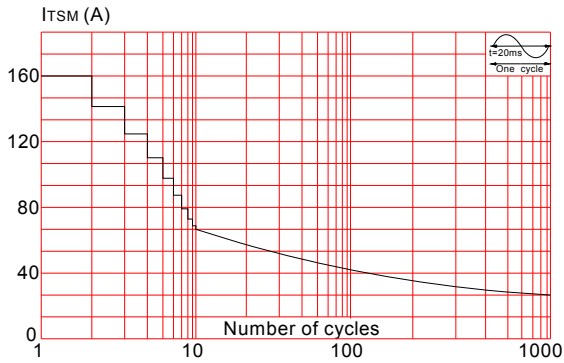


FIG.4: On-state characteristics (maximum values)

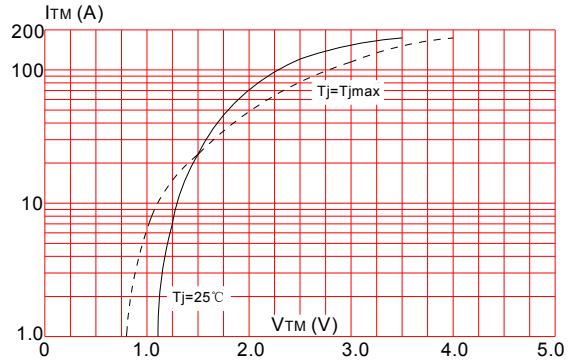


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

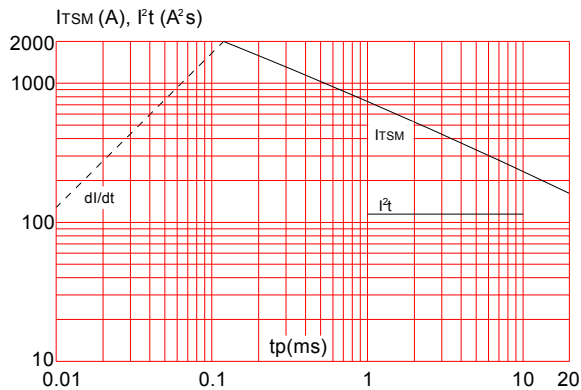


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

